

2STA1694

High power PNP epitaxial planar bipolar transistor

Features

- High breakdown voltage V_{CEO} = -120 V
- Complementary to 2STC4467
- Fast-switching speed
- Typical f_t = 20 MHz
- Fully characterized at 125 °C

Applications

Audio power amplifier

Description

The device is a PNP transistor manufactured using new BiT-LA (Bipolar transistor for linear amplifier) technology. The resulting transistor shows good gain linearity behaviour.

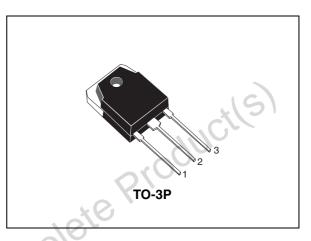


Figure 1. Internal schematic diagram

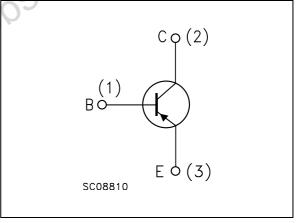


Table 1.	Device summary
	Device Summary

Order code	Marking	Package	Packaging
2STA1694	2STA1694	TO-3P	Tube

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Electrical ratings 1

Table 2.	Absolute maximum ratings				
Symbol	Parameter	Value	Unit		
V _{CBO}	Collector-base voltage (I _E = 0)	-120	V		
V _{CEO}	Collector-emitter voltage (I _B = 0)	-120	V		
V _{EBO}	Emitter-base voltage (I _C = 0) -6				
Ι _C	Collector current -8				
I _{CM}	Collector peak current (t _P < 5 ms) -16				
P _{TOT}	Total dissipation at $T_c = 25 \text{ °C}$ 80				
T _{stg}	Storage temperature -65 to 150		°C		
Τ _J	Max. operating junction temperature	150	°C		
Table 3.	Thermal data				

Table 3. Thermal data

Symbol		Parameter	6,	Value	Unit
	R _{thj-case}	Thermal resistance junction-case	max	1.563	°C/W
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2 Electrical characteristics

(T_{case} = 25 °C; unless otherwise specified)

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
I _{CBO}	Collector cut-off current $(I_E = 0)$	V _{CB} = -120 V			-10	μA
I _{EBO}	Emitter cut-off current (I _C = 0)	V _{EB} = -6 V			-10	μA
V _{(BR)CEO} ⁽¹⁾	Collector-emitter breakdown voltage (I _B = 0)	I _C = -50 mA	-120			V
V _{(BR)CBO}	Collector-base breakdown voltage (I _E = 0)	I _C = -100 μA	-120	00		V
V _{(BR)EBO} ⁽¹⁾	Emitter-base breakdown voltage (I _C = 0)	I _E = -1 mA	-6			V
V _{CE(sat)} ⁽¹⁾	Collector-emitter saturation voltage	I _C = -3 A I _B = -300 mA			-1.5	V
h _{FE}	DC current gain	$I_{C} = -3 A$ $V_{CE} = -4 V$	70		140	
f _T	Transition frequency	$I_{C} = -0.5 \text{ A} \text{ V}_{CE} = -12 \text{ V}$		20		MHz

Table 4. Electrical characteristics

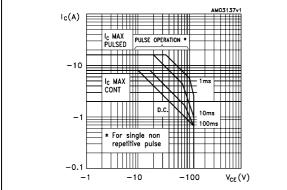
1. Pulsed duration = 300 μs, duty cycle ≤ 1.5%

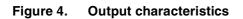
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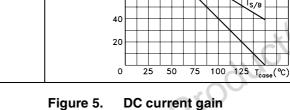
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Electrical characteristics (curves) 2.1

Figure 2. Safe operating area







P_{tot} (%)

100

80

60

Derating curve

Figure 3.

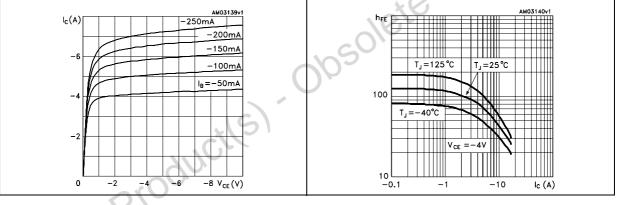
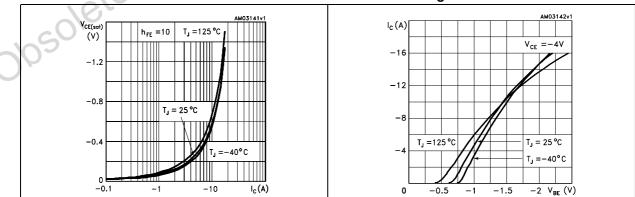


Figure 6. Collector-emitter saturation voltage Figure 7. voltage

Collector current vs base-emitter



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3 Package mechanical data

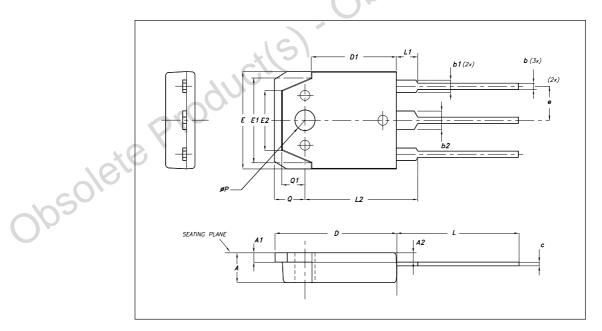
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DIM.		mm.	
	MIN.	ТҮР	MAX.
A	4.6		5
A1	1.45	1.50	1.65
A2	1.20	1.40	1.60
b	0.80	1	1.20
b1	1.80		2.20
b2	2.80		3.20
С	0.55	0.60	0.75
D	19.70	19.90	20.10
D1		13.90	
E	15.40		15.80
E1		13.60	
E2		9.60	
e	5.15	5.45	5.75
L	19.50	20	20.50
L1		3.50	2
L2	18.20	18.40	18.60
P	3.10		3.30
Q		5	





4 Revision history

Table 5. Document revision history

	Date	Revision	Changes
	23-Nov-2007	1	Initial release
	15-May-2008	2	Document status promoted from preliminary data to datasheet.
	09-Feb-2009	3	Added section 2.1: Electrical characteristics (curves).
0050	etepro	duct	Added section 2.1: Electrical characteristics (curves).



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